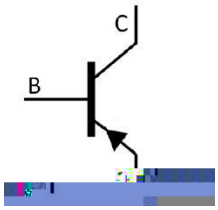
WR0<5 ṂṂ Ḅ SQS ÆṀ ч s ‖ ㄱ Silicon PNP transistor in a TO-92 Plastic Package.

ǎ я ㄡ/ ت ᄃ я ∪ Ң/ق ɔ ‖ ژ ɔ ķ Ң/ љ PSVD75J Ѝ ´ ņ ғ β
High voltage low saturation, low collector output capacitance, complementary pair with MPSA42G. HF Product.

ᵬ ㄡ ɔ я í ɔ ت
High voltage control circuit.





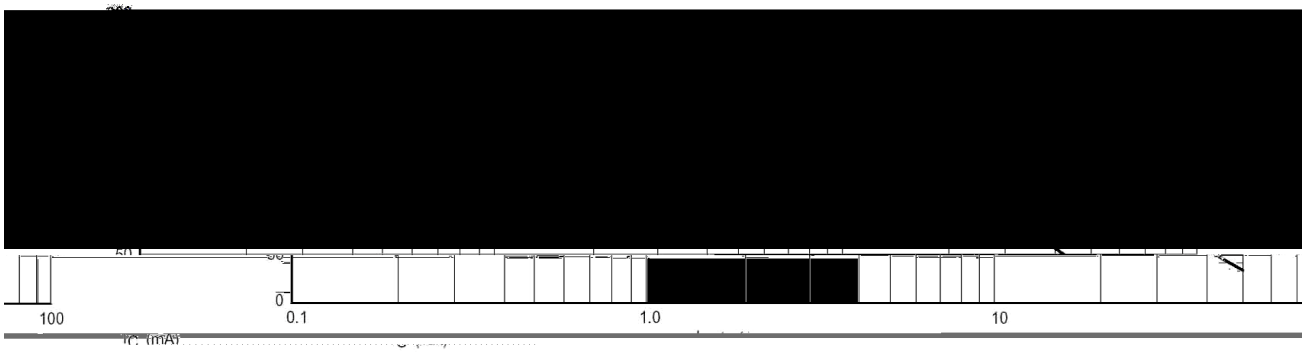
PIN1 χ Collector PIN 2 χ Base PIN 3 χ Emitter

v ‘Ω Parameter	٧ N Symbol	‘Ω Ö Rating	D Ч Unit
Collector to Base Voltage	V_{CBO}	-300	V
Collector to Emitter Voltage	V_{CEO}	-300	V
Emitter to Base Voltage	V_{EBO}	-5.0	V
Collector Current - Continuous	I_C	-500	mA
Base Current - Continuous	I_B	-30	mA
Collector Power Dissipation	P_C	625	mW
Collector Power Dissipation	$P_C(T_C=25$ ł)	1.5	W
Junction Temperature	T_j	150	
Storage Temperature Range	T_{stg}	-55 150	

v ‘Ω Parameter	٧ N Symbol	‡ ;ł ţ Test Conditions	ώ ņ Ö Min	Ε ʒ Ö Typ	ώ ² Ö Max	D Ч Unit
Collector to Base Breakdown Voltage	V_{CBO}	I_C=-100				

/ Electrical Characteristic Curve

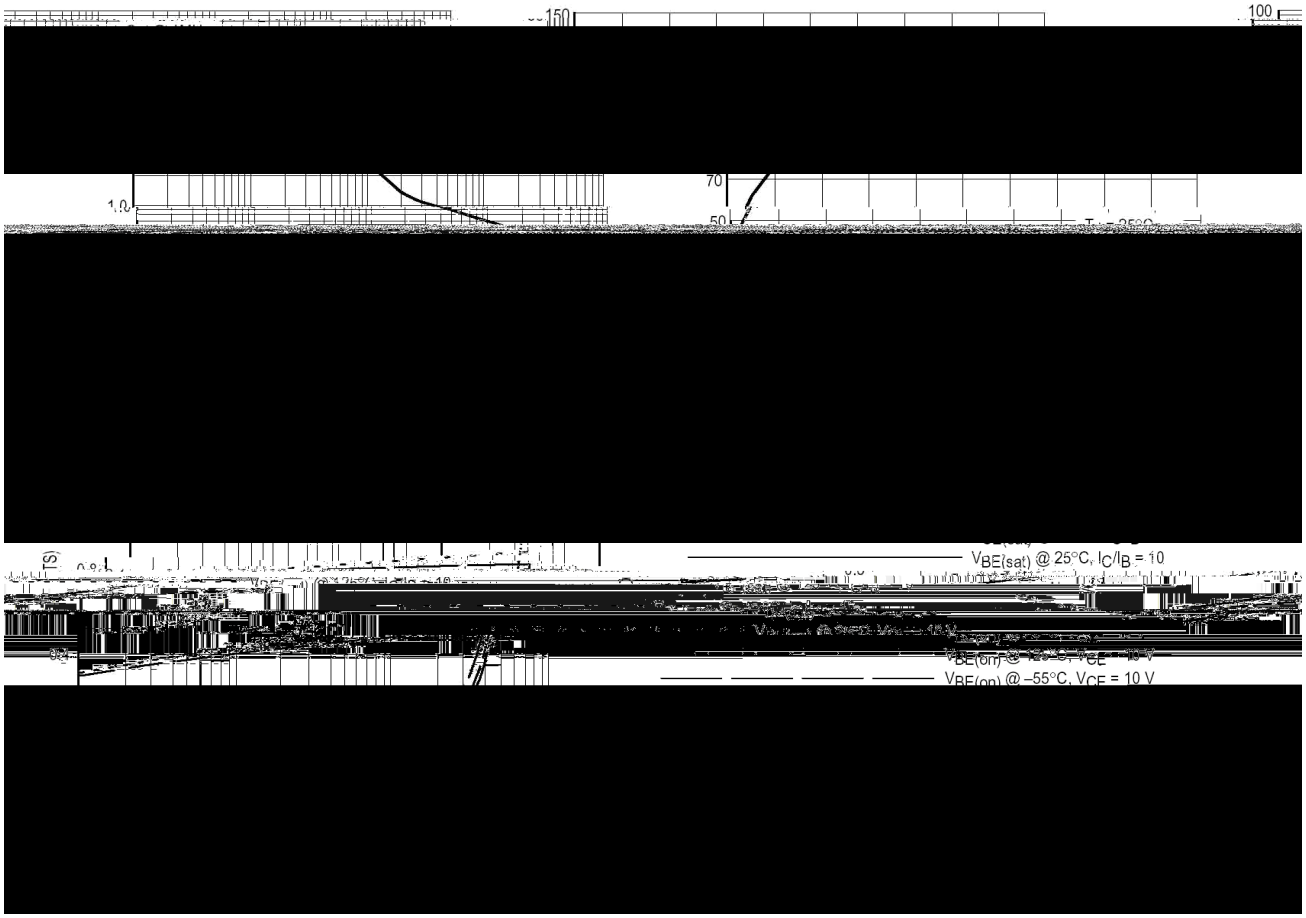
h_{FE} – I_C



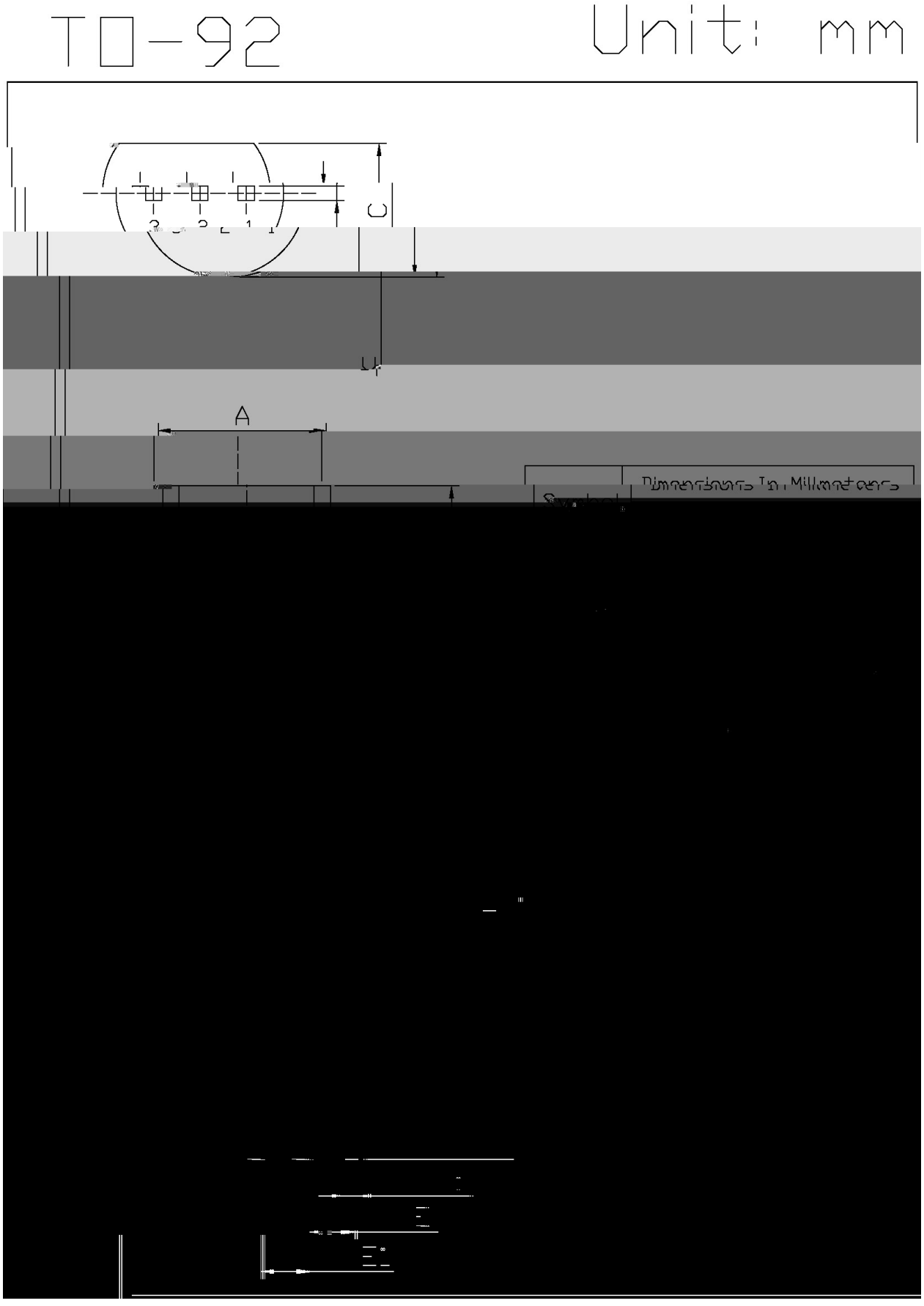
C_{ob} – V_{CB}

C_{ib} – V_{CB}

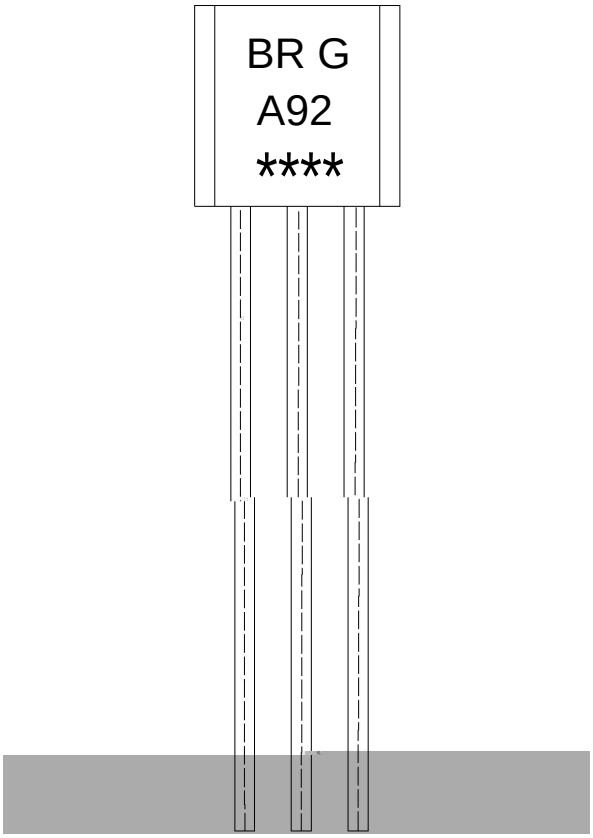
f_T – I_C



/ Package Dimensions



/ Marking Instructions



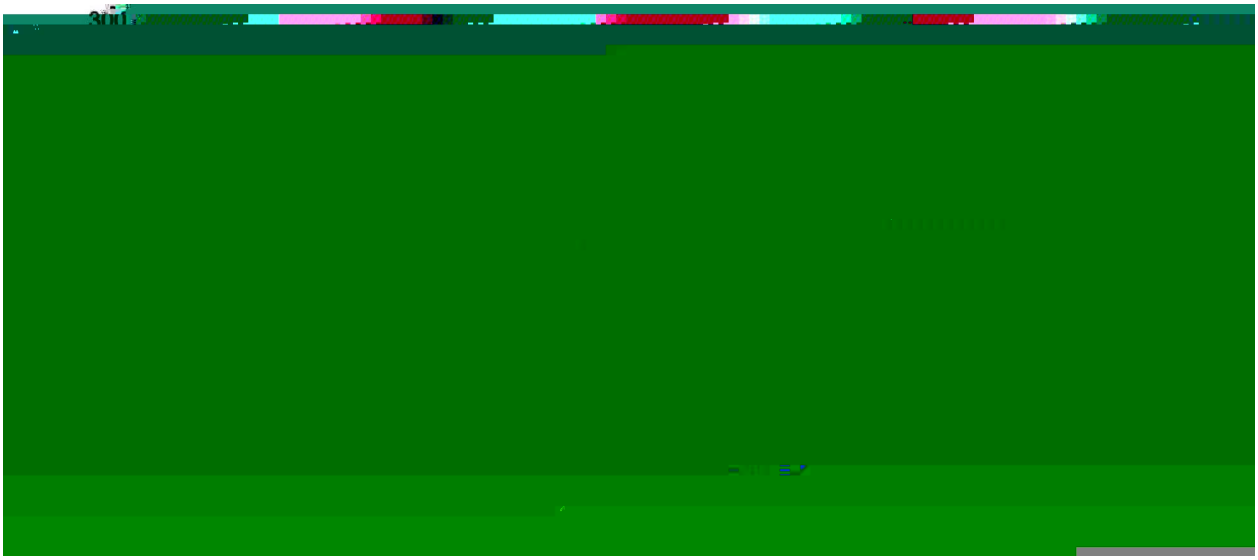
ب ˝ χ

EU=	ﻫ ३ И Ґ
D<5 χ	ﻫ ʒ N Ґ
J=	ﻫ ὴ ɾ β Ґ
---- χ	ﻫ ɨ ɾ ή N Ґ ɪ ɕ ɨ ɾ ή N Ψ ק

Note:

BR:	Company Code.
A92:	Product Type.
G:	Halogen Free Product
****:	Lot No. Code,code change with Lot No.

( ) / Temperature Profile for Dip Soldering(Pb-Free)



ب ˝ χ

1 Ĺ ♬ □ ỷ 25 Ḱ 150 ɬ ı `H ڑ 60 Ḱ 90sec;

2 Š Ө □ ỷ 255 ° 5 ɬ ı `H ڑ `Y ʌ ʁ 5 ° 0.5sec;

3 ì ˙ ϒ ˛ ɔ ѡ ỷ ʁ 2 Ḱ 10 ɬ /sec.

Note:

1.Preheating:25~150 ɬ , Time:60~90sec.

2.Peak Temp.:255 ° 5 ɬ , Duration:5 ° 0.5sec.

3. Cooling Speed: 2~10 ɬ /sec.

/ Resistance to Soldering Heat Test Conditions

□ ỷ χ 270 ° 5 ɬ `H ڑ χ 10 ° 1 sec. Temp:270±5 Time:10±1 sec

/ Packaging SPEC.

Ѝ Ω ţ ϒ Ь / BULK

Package Type	Units					Dimension		(unit mm3)
	Units/Bag /	Bags/Inner Box /	Units/Inner Box /	Inner Boxes/Outer Box /	Units/Outer Box /	Bag	Inner Box	Outer Box
TO-92	1,000	10	10,000	5	50,000	135×190	237×172×102	560×245×195
	1,000	10	Bag6	re10	T8(600023	T8ag)14(0,590)75(	)13384(237×172×)79(102)75(	)9173(560×245